

SOT-323 PNP Silicon PNP transistor in a SOT-323 Plastic Package.

High voltage, complementary Pair with MMBT5551W.

General purpose high voltage amplifier.



PIN1	Emitter	PIN 2	Base	PIN 3	Collector
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h _{FE} Classifications	A	B	C
Symbol			
h _{FE} Range	50 150	100 300	200 400
Marking	H2LA	H2LB	H2LC

静态特性

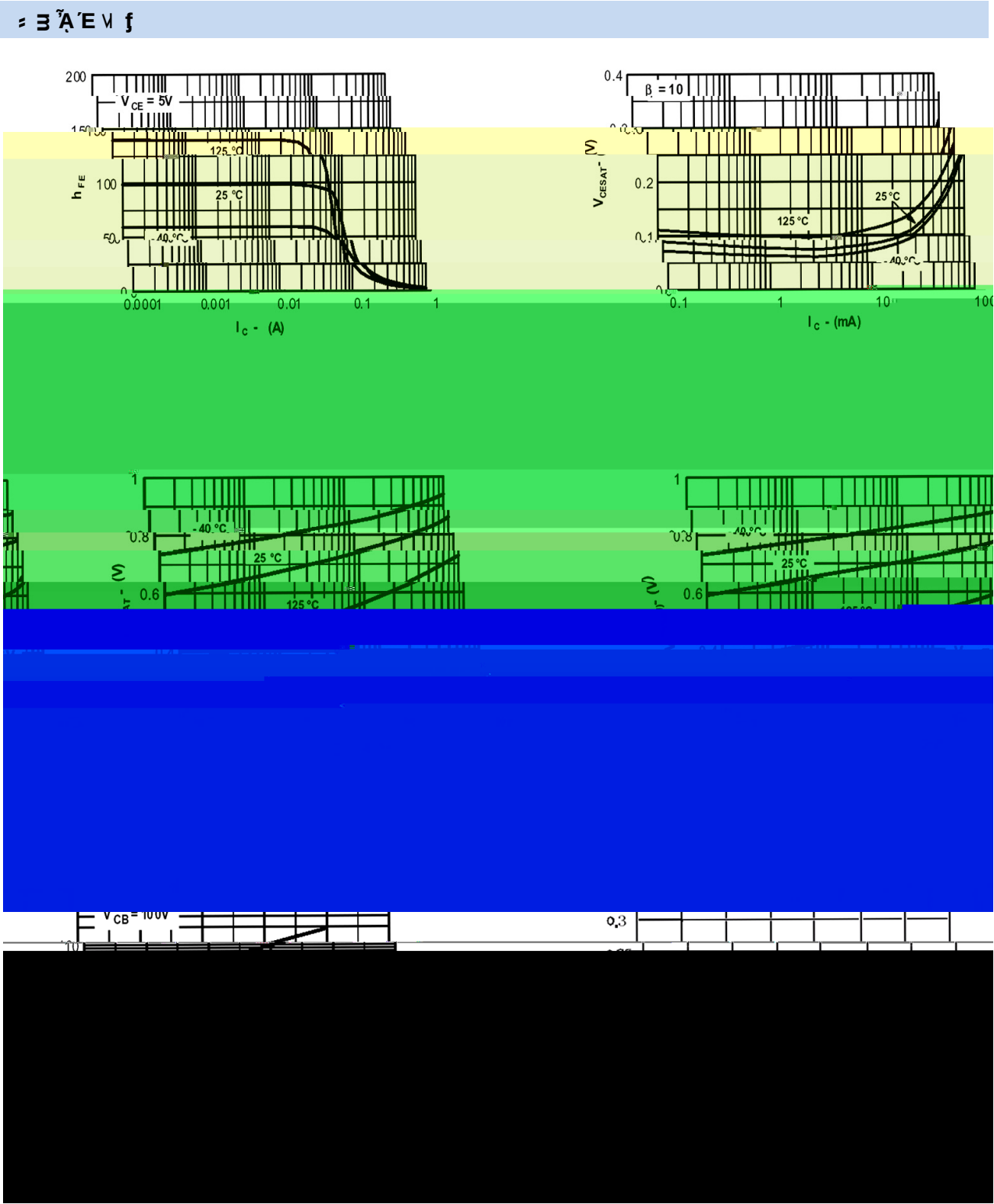
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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-180	V
Collector to Emitter Voltage	V_{CEO}	-160	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-600	mA
Base Current - Continuous	I_B	-300	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

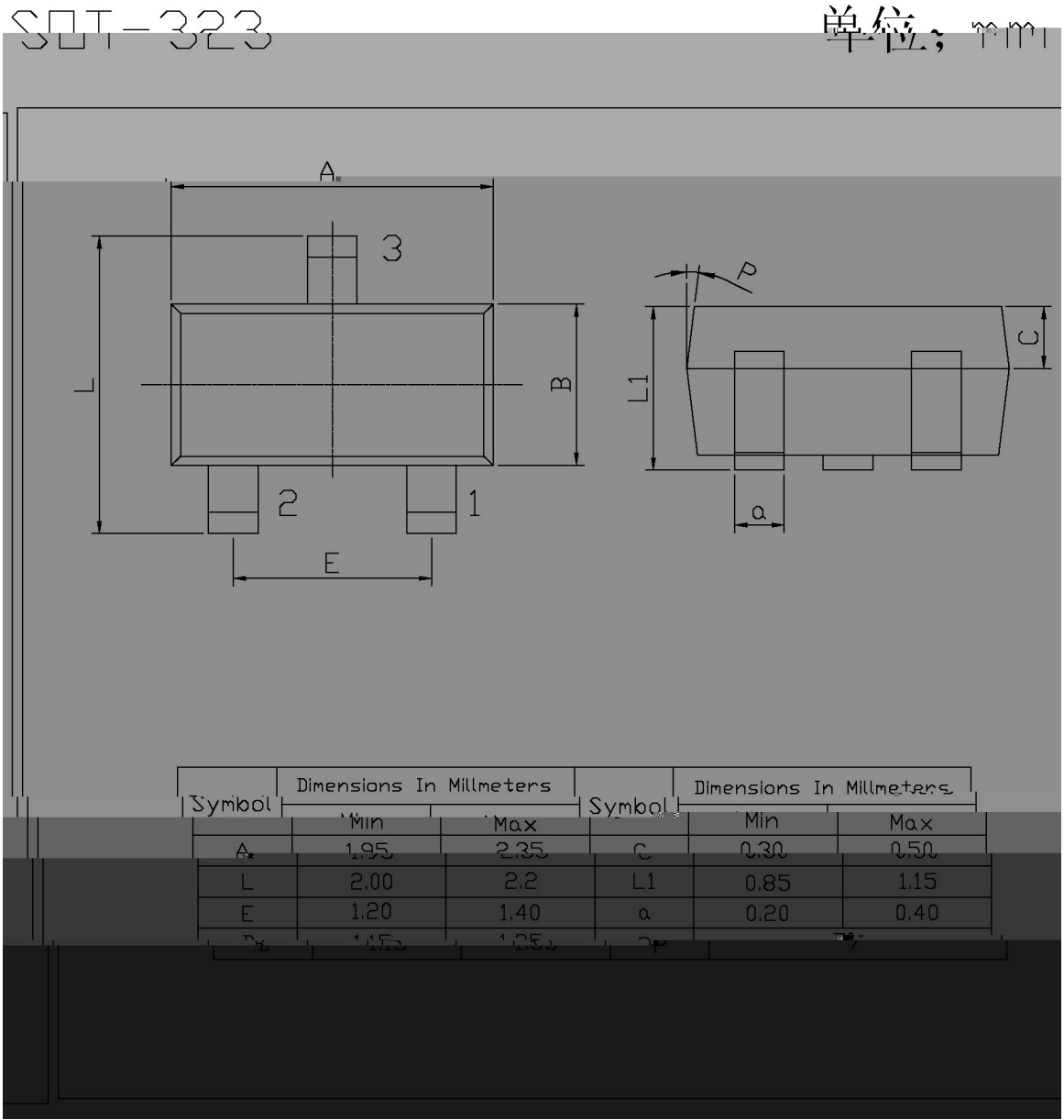
动态特性

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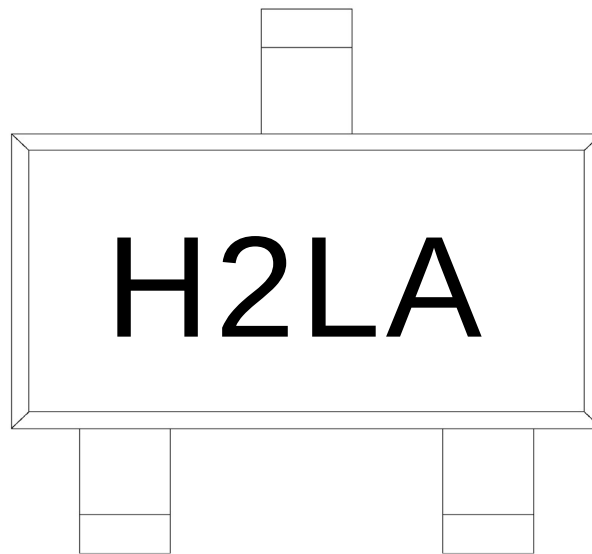
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-180V$ $I_E=0$			-0.1	μA
Emitter to Base Current	I_{EBO}	$V_{EB}=-6.0V$ $I_C=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-5.0V$ $I_C=-10mA$	50	200	400	
	$h_{FE(2)}$	$V_{CE}=-5.0V$ $I_C=-50mA$	20	70		
	$h_{FE(3)}$	$V_{CE}=-5.0V$ $I_C=-1.0mA$	40	180		
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-10mA$ $I_B=-1.0mA$		-0.12	-0.4	V
	$V_{CE(sat)(2)}$	$I_C=-50mA$ $I_B=-5.0mA$		-0.5	-0.8	V
Base to Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C=-10mA$ $I_B=-1.0mA$		-0.75	-1.0	V
	$V_{BE(sat)(2)}$	$I_C=-50mA$ $I_B=-5.0mA$		-0.8	-1.0	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=-5.0V$ $I_C=-10mA$		-0.7	-0.75	V
Transition Frequency	f_T	$V_{CE}=-10V$ $I_E=-10mA$	50	80		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V$ $I_E=0$ $f=10MHz$		2.5	5.0	pF
Turn-On Time	t_{on}	$I_C=-100mA$ $-I_{B1}=I_{B2}=-10mA$		0.1		μs
Turn-Off Time	t_{off}			0.2		μs
Storage Time	t_{stg}			0.1		μs



单位：mm



1. 符号



H

2L

A h_{FE}

Note:

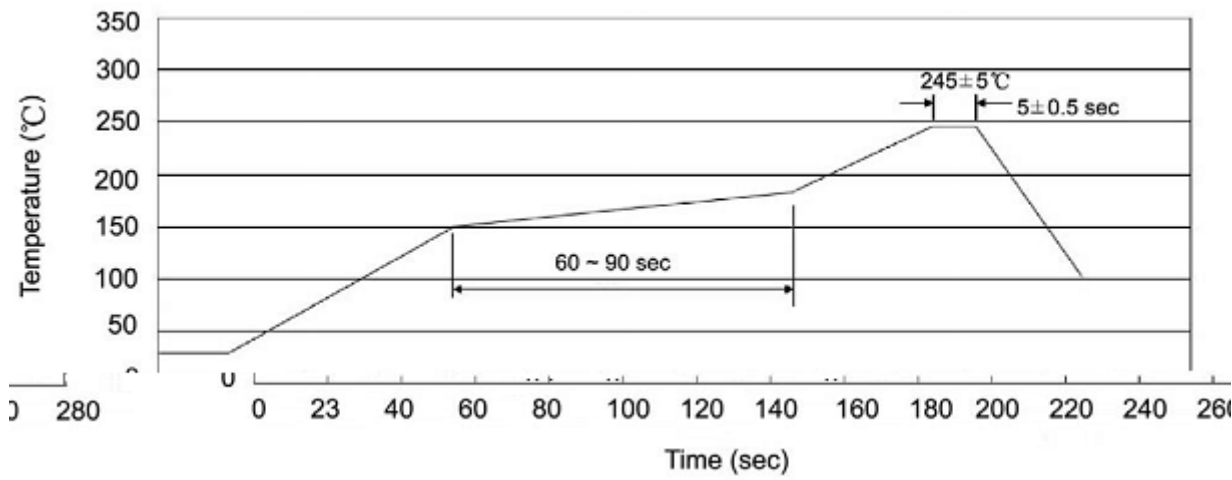
H: Company Code.

2L: Product Type.

A h_{FE} Classifications Symbol

温度冲击试验

Whp shudwxuh Suriloh i ru LU Uhior z Vroghulqj+Se0lueh,



Note:

1	25	150	60
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